

L Number	Hits	Search Text	DB	Time stamp
3	212	((wafer and (metal adj (film or layer)) and (attach\$5 or bond\$4) and ((balls adj grid adj arrays) or (BGA)) and semiconductor and (dic\$4 or cut\$4 or separat\$5)) and @ad<=20000616) and (dic\$5 or cut\$6 or saw\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 09:00
5	172	((wafer and (metal adj (film or layer)) and (attach\$5 or bond\$4) and ((balls adj grid adj arrays) or (BGA)) and semiconductor and (dic\$4 or cut\$4 or separat\$5)) and @ad<=20000616) and (dic\$5 or cut\$6 or saw\$5)) and dic\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 09:24
6	92	((wafer and (metal adj (film or layer)) and (attach\$5 or bond\$4) and ((balls adj grid adj arrays) or (BGA)) and semiconductor and (dic\$4 or cut\$4 or separat\$5)) and @ad<=20000616) and (dic\$5 or cut\$6 or saw\$5)) and (dicing or diced)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 09:35
7	70	((wafer and (metal adj (film or layer)) and (attach\$5 or bond\$4) and ((balls adj grid adj arrays) or (BGA)) and semiconductor and (dic\$4 or cut\$4 or separat\$5)) and @ad<=20000616) and (dic\$5 or cut\$6 or saw\$5)) and (dicing or diced)) and (individual\$3 or each)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 09:36
8	70	((wafer and (metal adj (film or layer)) and (attach\$5 or bond\$4) and ((balls adj grid adj arrays) or (BGA)) and semiconductor and (dic\$4 or cut\$4 or separat\$5)) and @ad<=20000616) and (dic\$5 or cut\$6 or saw\$5)) and (dicing or diced)) and (individual\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 09:36
9	6	((wafer and (metal adj (film or layer)) and (attach\$5 or bond\$4) and ((balls adj grid adj arrays) or (BGA)) and semiconductor and (dic\$4 or cut\$4 or separat\$5)) and @ad<=20000616) and (dic\$5 or cut\$6 or saw\$5)) and (dicing or diced)) and (individual\$3 adj device)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 09:37
-	348	(438/15).CCLS.	USPAT	2003/05/20 07:57
-	258	(438/113).CCLS.	USPAT	2002/07/03 08:58
-	94	(438/110).CCLS.	USPAT	2002/07/03 08:58
-	59	(438/114).CCLS.	USPAT	2002/07/03 08:58
-	681	438/15,110,113,114.ccls.	USPAT	2002/12/19 14:38
-	401	438/15,110,113,114.ccls. and test\$3	USPAT	2001/08/07 15:09
-	272	(438/15,110,113,114.ccls. and test\$3) and (dice\$4 or cut\$5)	USPAT	2001/08/07 15:10
-	901	438/15,110,113,114.ccls.	USPAT; EPO; JPO; DERWENT	2002/02/04 09:53
-	460	438/15,110,113,114.ccls. and test\$3	USPAT; EPO; JPO; DERWENT	2002/02/04 09:54
-	325	(438/15,110,113,114.ccls. and test\$3) and (dic\$5 or cut\$5)	USPAT; EPO; JPO; DERWENT	2002/02/05 08:26
-	5	(("6077757") or ("6335224") or ("6309943") or ("6309909") or ("6326697")).PN.	USPAT	2003/05/21 08:46
-	7	(("6077757") or ("6335224") or ("6309943") or ("6309909") or ("6326697") or ("5858815") or ("5137836")).PN.	USPAT	2002/02/05 09:49
-	326	(438/15,110,113,114.ccls. and test\$3) and (dic\$5 or cut\$5)	USPAT; EPO; JPO; DERWENT	2002/02/05 08:28
-	0	((438/15,110,113,114.ccls. and test\$3) and (dic\$5 or cut\$5)) and (magnet\$7 adj align\$5)	USPAT; EPO; JPO; DERWENT	2002/02/05 08:33
-	170	((438/15,110,113,114.ccls. and test\$3) and (dic\$5 or cut\$5)) and (align\$5)	USPAT; EPO; JPO; DERWENT	2002/02/05 08:32

-	2705	magnet\$7 adj align\$5	USPAT; EPO; JPO; DERWENT	2002/02/05 08:56
-	0	(magnet\$7 adj align\$5) and (wafer adj20 dielectric adj tape)	USPAT; EPO; JPO; DERWENT	2002/02/05 08:37
-	0	wafer adj20 dielectric adj tape	USPAT; EPO; JPO; DERWENT	2002/02/05 08:37
-	0	wafer adj dielectric adj tape	USPAT; EPO; JPO; DERWENT	2002/02/05 08:38
-	248	(magnet\$7 adj align\$5) and semiconductor	USPAT; EPO; JPO; DERWENT	2002/02/05 08:57
-	0	((magnet\$7 adj align\$5) and ring) and (charged adj slot)	USPAT; EPO; JPO; DERWENT	2002/02/05 08:49
-	0	(magnet\$7 adj align\$5) and (charged adj slot)	USPAT; EPO; JPO; DERWENT	2002/02/05 08:49
-	613	(magnet\$7 adj align\$5) and ring	USPAT; EPO; JPO; DERWENT	2002/02/05 08:50
-	47	((magnet\$7 adj align\$5) and ring) and semiconductor	USPAT; EPO; JPO; DERWENT	2002/02/05 08:51
-	3066	optically adj align\$5	USPAT; EPO; JPO; DERWENT	2002/02/05 08:56
-	612	(optically adj align\$5) and semiconductor	USPAT; EPO; JPO; DERWENT	2002/02/05 08:57
-	8	((("6077757") or ("6335224") or ("6309943") or ("6309909") or ("6326697") or ("5858815") or ("5137836") or ("4781969")).PN.	USPAT	2003/05/20 08:12
-	10260	wood.inv.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/03 08:13
-	539	wood.inv. and alan	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/03 08:13
-	232	(wood.inv. and alan) and (micron adj technology)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/03 08:14
-	1	("6268650").PN.	USPAT	2002/12/20 10:24
-	425	(438/15).CCLS.	USPAT	2002/07/08 08:43
-	331	(438/113).CCLS.	USPAT	2002/07/08 08:57
-	140	(438/110).CCLS.	USPAT	2002/07/08 08:57
-	90	(438/114).CCLS.	USPAT	2002/07/08 08:57
-	425	(438/15).CCLS.	USPAT	2002/07/08 08:43
-	331	(438/113).CCLS.	USPAT	2002/07/08 08:57
-	140	(438/110).CCLS.	USPAT	2002/07/08 08:57
-	90	(438/114).CCLS.	USPAT	2002/07/08 14:32
-	13	((("6389689") or ("5977629") or ("5796170") or ("6326700") or ("6268650") or ("5858815") or ("5817535") or ("5770032") or ("4781969") or ("5073840") or ("5696033") or ("5834839") or ("6160714")).PN.	USPAT	2002/07/08 10:35
-	8	((("6309909") or ("5858815") or ("5137836") or ("6077757") or ("6326697") or ("6165885") or ("5834320") or ("4781969")).PN.	USPAT	2002/07/09 09:56

-	0	(wafer adj (bond\$3 or attach\$3) near4 (dielectric adj (layer or film))) same test\$3 same (cut\$4 or dic\$3 or separat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/19 15:00
-	0	(wafer adj (bond\$3 or attach\$3) near4 (dielectric adj (layer or film))) same test\$3 same (cut\$4 or dic\$3 or separat\$3)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/19 14:07
-	19	wafer adj (bond\$3 or attach\$3) near4 (dielectric adj (layer or film))	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/19 14:07
-	0	(wafer adj (bond\$3 or attach\$3) near4 (dielectric adj (layer or film))) same test\$3	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/19 14:38
-	963	438/15,110,113,114.ccls.	USPÄT	2002/12/19 14:38
-	1212	438/15,110,113,114.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/19 14:38
-	0	438/15,110,113,114.ccls. and ((wafer adj (bond\$3 or attach\$3) near4 (dielectric adj (layer or film))) same test\$3)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/19 14:40
-	9	(wafer adj (dielectric adj (layer or film))) same test\$3	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/20 08:18
-	13	((("5834839") or ("6389689") or ("6160714") or ("5977629") or ("6326700") or ("6268650") or ("5858815") or ("5817535") or ("5770032") or ("5796170") or ("4781969") or ("5073840") or ("5696033")).PN.	USPAT	2002/12/19 15:19
-	85	wafer same dielectric same test\$3 same (cut\$3 or dic\$3 or slic\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/20 08:42
-	78	(wafer same dielectric same test\$3 same (cut\$3 or dic\$3 or slic\$3)) and semiconductor	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/20 09:38
-	348	(wafer same (dielectric adj (layer or film))) same test\$3	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/20 09:35
-	322	((wafer same (dielectric adj (layer or film))) same test\$3) and semiconductor	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/20 09:38
-	98	((wafer same (dielectric adj (layer or film))) same test\$3) and semiconductor) and (cut\$3 or dic\$3)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/20 09:39
-	1	("6424023").PN.	USPÄT	2002/12/20 10:24
-	3	((("5897337") or ("5858815") or ("6389689")).PN.	USPAT	2002/12/23 11:53
-	2	((("5897337") or ("6389689")).PN.	USPAT	2002/12/23.11:53

-	9187	((balls adj grid adj arrays) or (BGA)) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/20 07:59
-	4418	((((balls adj grid adj arrays) or (BGA)) and semiconductor) and (dic\$4 or cut\$4 or separat\$5))	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/20 08:02
-	4476	((((balls adj grid adj arrays) or (BGA)) and semiconductor) and (dic\$4 or cut\$4 or separat\$5 or saw\$4))	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/20 08:04
-	955	(((((balls adj grid adj arrays) or (BGA)) and semiconductor) and (dic\$4 or cut\$4 or separat\$5)) and (metal adj (film or layer)))	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/20 08:04
-	970	(((((balls adj grid adj arrays) or (BGA)) and semiconductor) and (dic\$4 or cut\$4 or separat\$5 or saw\$4)) and (metal adj (film or layer)))	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/20 08:04
-	1	("20010052642").PN.	US-PGPUB	2003/05/20 08:12
-	472	wafer and (metal adj (film or layer)) and (attach\$5 or bond\$4) and ((balls adj grid adj arrays) or (BGA)) and semiconductor and (dic\$4 or cut\$4 or separat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/20 08:52
-	233	((wafer and (metal adj (film or layer)) and (attach\$5 or bond\$4) and ((balls adj grid adj arrays) or (BGA)) and semiconductor and (dic\$4 or cut\$4 or separat\$5)) and @ad<=20000616	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/20 08:55
-	212	((wafer and (metal adj (film or layer)) and (attach\$5 or bond\$4) and ((balls adj grid adj arrays) or (BGA)) and semiconductor and (dic\$4 or cut\$4 or separat\$5)) and @ad<=20000616) and (dic\$5 or cut\$6 or saw\$5)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 08:23
-	206	((wafer and (metal adj (film or layer)) and (attach\$5 or bond\$4) and ((balls adj grid adj arrays) or (BGA)) and semiconductor and (dic\$4 or cut\$4 or separat\$5)) and @ad<=20000616) and (dic\$5 or cut\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/20 09:06
-	1	((wafer adj semiconductor) same (metal adj (film or layer)) same (attach\$5 or bond\$4) same ((balls adj grid adj arrays) or (BGA)) same (dic\$4 or cut\$4 or separat\$5)) same (dic\$5 or cut\$6 or saw\$5)) and @ad<=20000616	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/20 10:06